

CMOS Pixel Sensors for High Precision Beam Telescopes and Vertex Detectors

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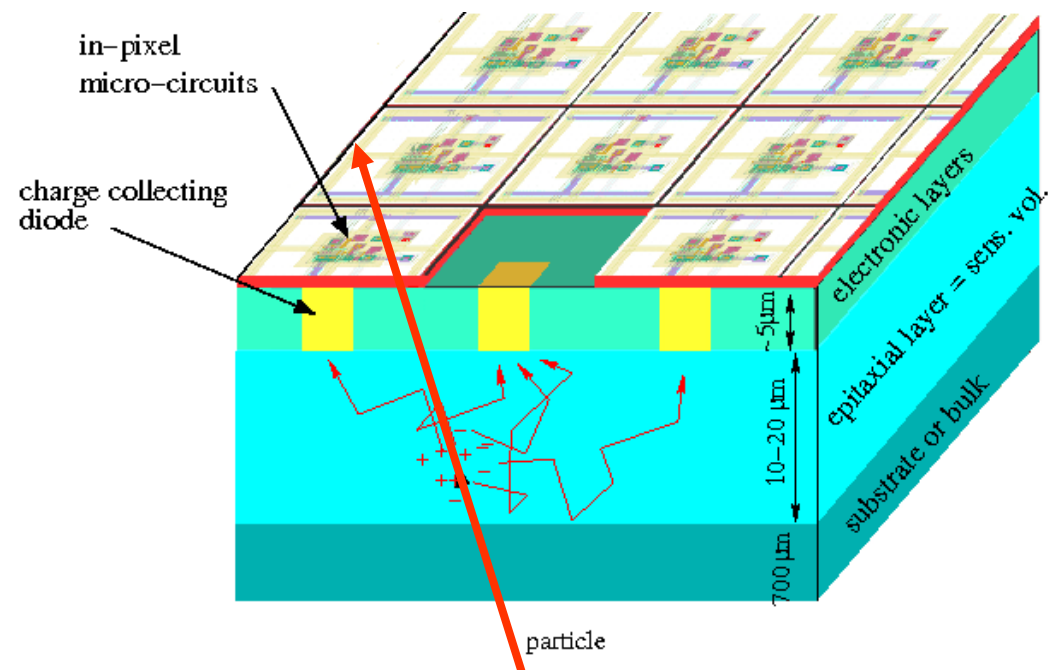
IPHC-Strasbourg

on behalf of the IPHC-IRFU collaboration

- Principle of operation
- Achievements and applications
- Developments
- Summary and conclusions

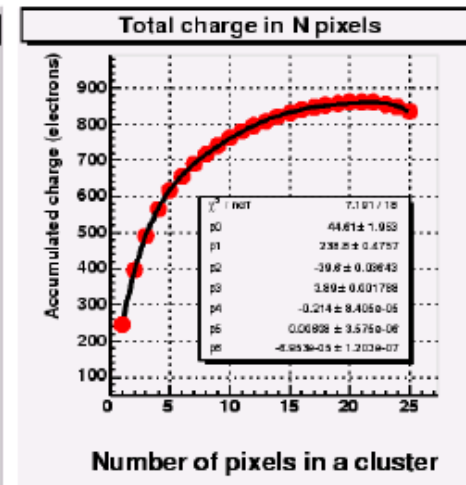
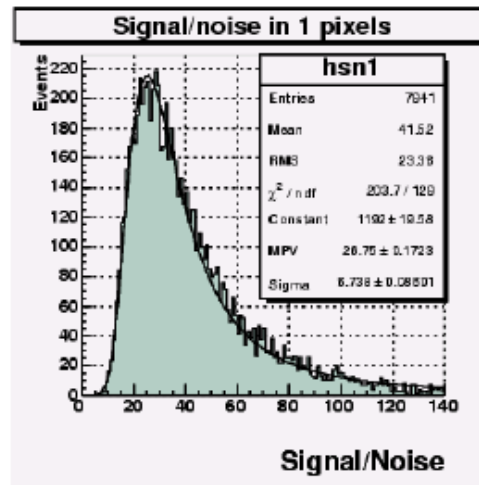
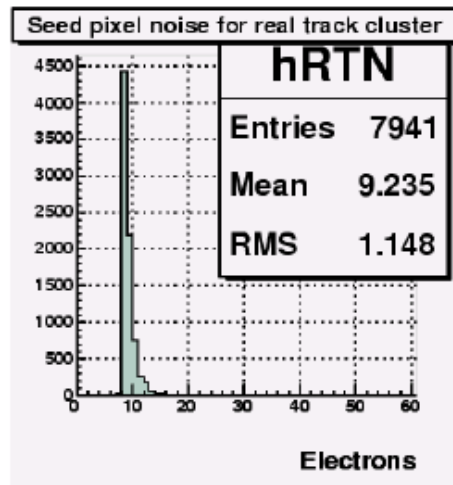
CMOS sensor principle

- Signal collection
 - Charges generated in epitaxial layer $\rightarrow \sim 1000 e^-$ for MIP
 - Charge carriers propagate thermally
 - In-pixel charge to signal conversion
- Advantages
 - High granularity
 - Thickness ($\sim O(50\mu\text{m})$)
 - Integrated signal processing
- Issues
 - Undepleted volume limitations
 - radiation tolerance
 - intrinsic speed
 - Small signal $O(100e^-)$ /pixel
 - In-pixel μ -circuits with NMOS transistors only



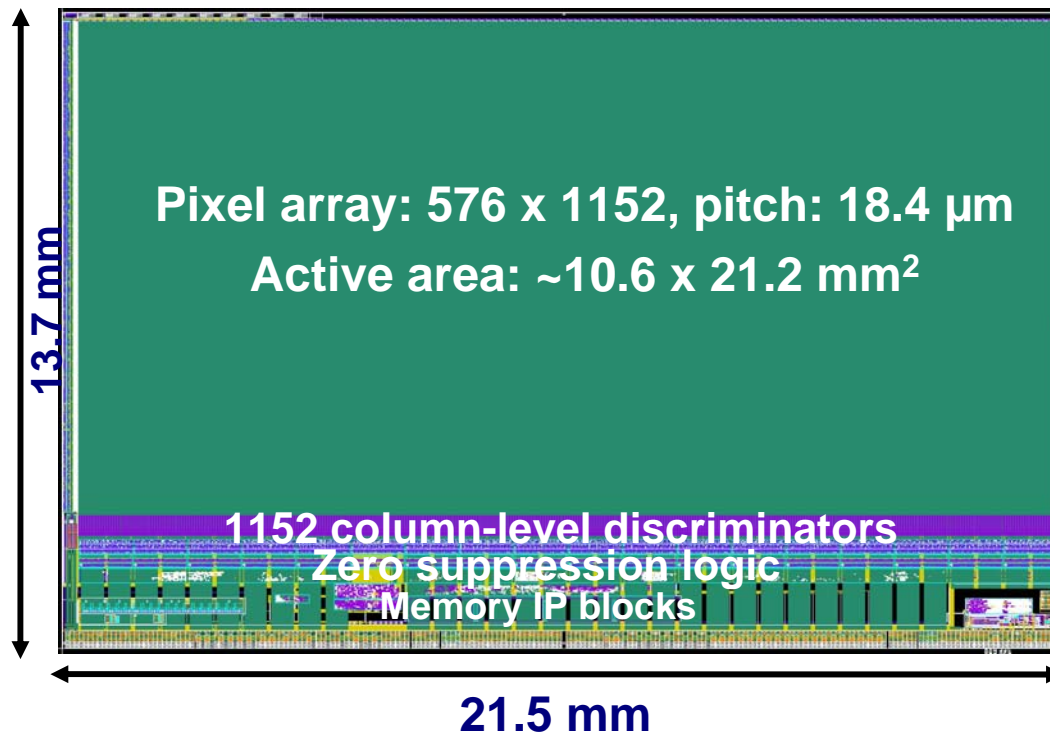
Basic performances

- more than 30 different sensors designed, fabricated and tested (lab & beam)
- extensive use of AMS 0.35 μm OPTO process
- room temperature operation
- noise $\sim 10\text{-}15e^-$
- S/N $\sim 15\text{-}30$
- detection efficiency $\sim 100\%$
- fake hit rate $\sim 10^{-4} - 10^{-5}$
- Radiation tol. $> 1\text{MRad}$ and $10^{13}n_{\text{eq}}/\text{cm}^2$ with $10\mu\text{m}$ pitch ($2 \times 10^{12}n_{\text{eq}}/\text{cm}^2$ with $20\mu\text{m}$ pitch)
- spatial resolution $1\text{-}5\mu\text{m}$ (pitch and charge-encoding dependent)



Mimosa 26

Fast full scale sensors: 10kFrame/s
column parallel architecture + integrated zero-suppression



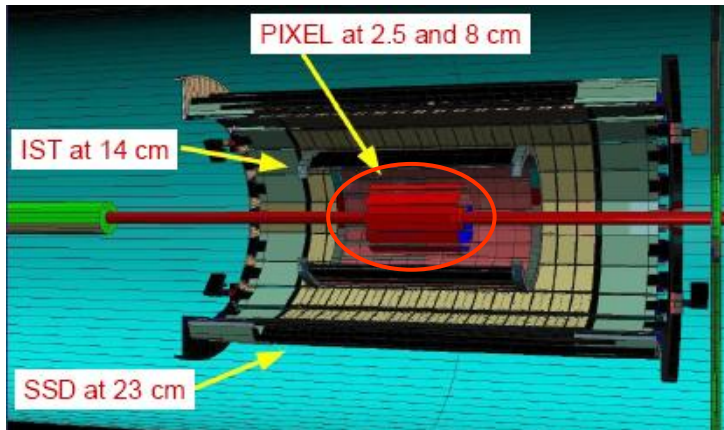
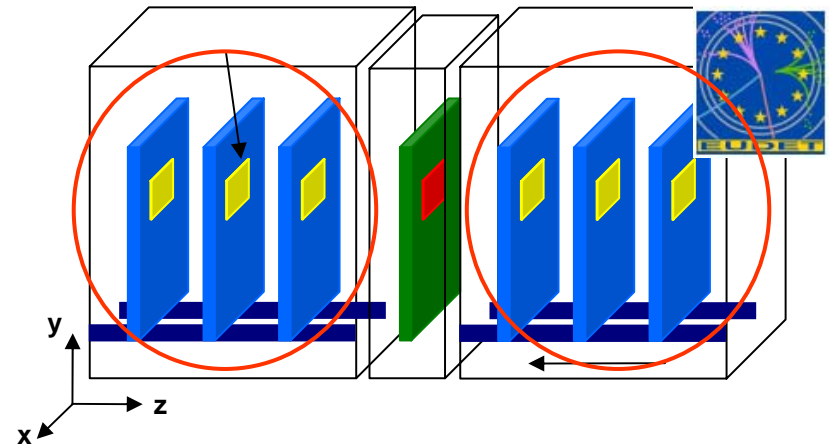
- binary output
(3.5-4 μm spatial resolution)
- in-pixel CDS +preamp.
- column level discrimination
- power dissipated $\sim 150 \text{ mW/cm}^2$
(rolling shutter)
- integration time $\sim 100\mu\text{s}$
- validated in lab

Characterisation @ CERN-SPS this summer

Mimosa 26 applications

- Reference planes of EUDET Beam Telescope

- Supported by EU FP6
- Infrastructure to support the ILC detector R&D
- Commissioning @ CERN summer 2009

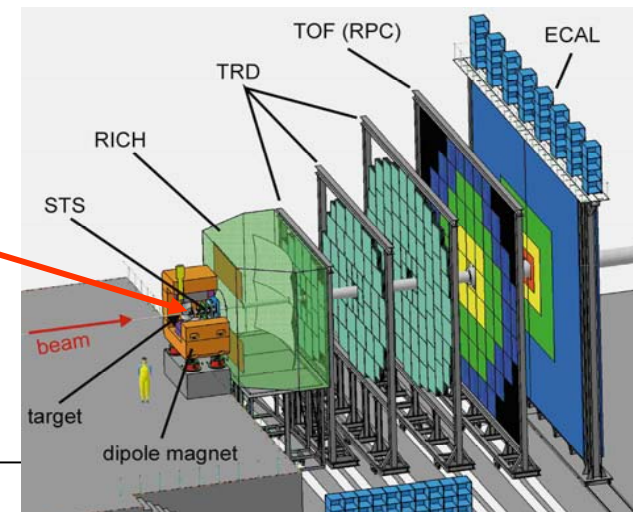


- STAR @ RHIC Heavy Flavour Tracker

- 1152 x 1024 pixels; 200 μ s integration time
- Submission end 2009
- First data 2011/2012

- CBM @ FAIR Micro Vertex Detector

- Double sided readout (40 \rightarrow 20 μ s integration time)
- Prototyping until 2012



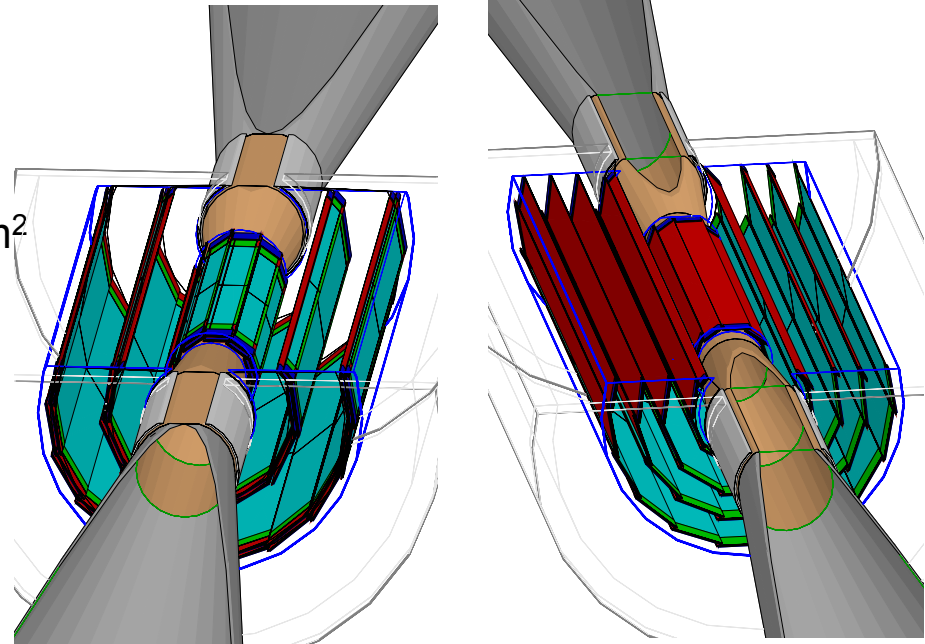
A VTX detector for the International Linear Collider

Physics requirements

- single point resolution $\sim 3\mu\text{m}$
- material budget $\sim 0.2\% X_0/\text{layer}$
- integration time 25 – 100 μs
- radiation tolerance $\sim 0.3\text{MRad}$, few $10^{11}n_{\text{eq}}/\text{cm}^2$

$$\sigma_{\text{IP}} = a \oplus b/p\sin^{3/2}\theta$$

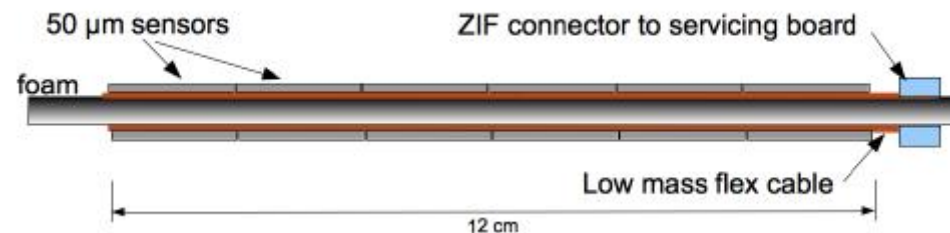
$a = 5\mu\text{m}$, $b = 10\mu\text{m GeV}$
(LHC $a = 12\mu\text{m}$, $b = 70\mu\text{m GeV}$)



A modified Mimosa 26

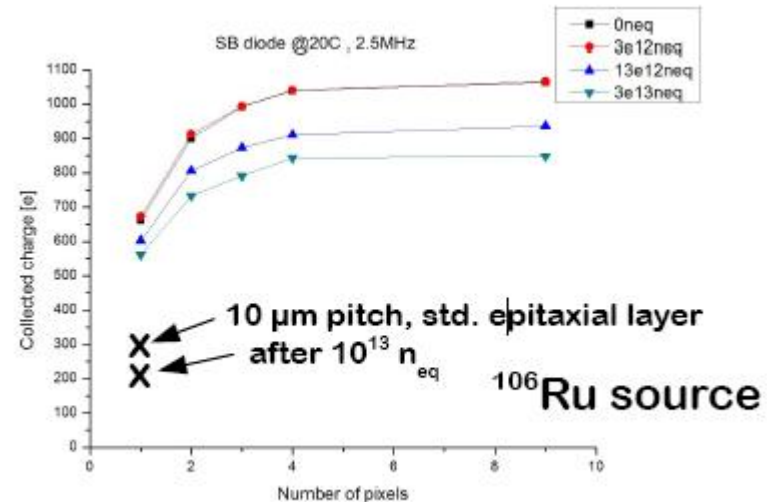
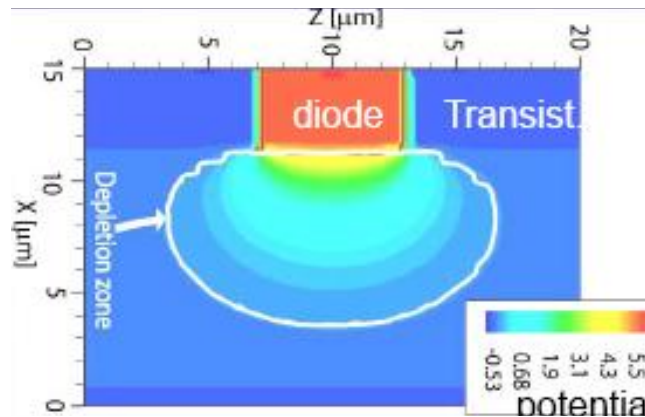
- Double sided readout
- 0.18 μm technology
- Integration issue \rightarrow PLUME project : double sided ladder equipped with 2x6 M26 (TDR 2012)
first prototype to be tested in SPS beam next November

$\sim 0.2 - 0.3\% X_0$



Further developments: Mimosa 25

- High resistivity epitaxial layer ($O(10^3) \Omega \cdot \text{cm}$) from XLAB $0.6 \mu\text{m}$ process



- $20 \mu\text{m}$ pixel pitch, $160 \mu\text{s}$ readout, $\sim 1 \text{ mm}^2$ sensitive area
- Cluster size $\sim 2 \times 2$ pixels (3×3 for low resistivity epi-layer)
- S/N ~ 50 for seed ($20-25$ for low resistivity epi-layer)
- S/N ~ 35 @ $10^{13} n_{\text{eq}}/\text{cm}^2$
- Improved tolerance to non-ionizing radiation (1-2 OM)
- Full characterization @ CERN-SPS this summer
- New: VDSM technology under study in coll. with CERN for sLHC

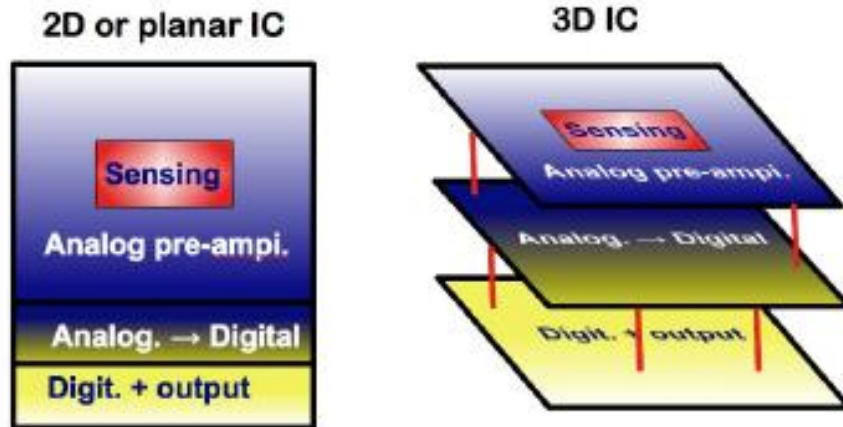
Further developments: 3D

Benefits:

- Increase integrated processing
- 100% sensitive area
- Select best process per layer task

To be assessed:

- Material budget?
- Power dissipation?



Example

- Tier1: charge collection
- Tier2: analog signal processing
- Tier3: digital signal processing
- Tier4: data transfer

FNAL + IN2P3 + INFN + ... consortium

First run (2 Tiers) submitted to Chartered-Tezzaron

Summary and conclusions

- Current CMOS sensors
 - Mature technology for real scale applications
 - High resolution, very low material budget
 - Application under way
 - EUDET-BT, STAR-HFT, CBM-MVD (R&D)
 - ILC-VTX (Option)
- New perspectives
 - Depleted sensitive volume (Non ionizing rad. tol. improved by >1 OM → sLHC)
 - 3D integration technology

More information on

<http://www.iphc.cnrs.fr/-CMOS-ILC-.html>